

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please cancel claims 1-26 and add new claims 27-52 in accordance with the following:

1-26 (cancelled)

27. (New). A system comprising:

an electrical component provided with at least one electrical contact surface;

an electrical insulating layer, which is disposed on the component, the electrical insulating layer having an opening to expose and surround a portion of the contact surface, wherein the insulating layer having a lateral surface that delimits the opening; and

an electrical connecting lead for electrically contacting the contact surface of the component, the electrical connecting lead comprising a metallization layer located on the lateral surface, such that the metallization layer meets the contact surface at an angle less than 90 degrees.

28. (New) The system as claimed in claim 27, wherein the metallization layer is oriented at an angle to the contact surface within a range of from 30° to 80°.

29. (New) The system as claimed in claim 27, wherein the metallization layer has a layer thickness within a range of from 0.5 µm to 30 µm.

30. (New) The system as claimed in claim 27, wherein the metallization layer has a multi-layered structure with at least two partial metallization layers arranged one upon the other.

31. (New) The system as claimed in claim 27, wherein the lateral surface of the insulating layer, on which the metallization layer is located has at least one step.

32. (New) The system as claimed in claim 27, wherein the insulating layer has a layer thickness within a range of from 20 µm to 500 µm.

33. (New) The system as claimed in claim 27, wherein the insulating layer has a multi-layered structure with at least two partial insulating layers arranged one on top of the other.

34. (New) The system as claimed in claim 27, wherein the insulating layer is formed by laminating at least one insulating foil onto the component.

35. (New) The system as claimed in claim 34, wherein
the lateral surface of the insulating layer faces the component,
at least one part of the insulating foil is laminated onto the component in such a way that
the insulating layer has a surface contour facing away from the component, and
a surface contour of the component is shown in the surface contour of the insulating foil
that faces away from the component.

36. (New) The system as claimed in claim 27, wherein the connecting lead has a section formed of a material different from the metallization layer, which section is located on the insulating layer and is provided with a thickness greater than that of the metallization layer.

37. (New) The system as claimed in claim 36, wherein the section of the connecting lead is electrodeposited.

38. (New) The system as claimed in claim 37, wherein the metallization layer and/or the section is formed of at least one metal selected from the group consisting of aluminum, gold, copper, molybdenum, silver, titanium and tungsten.

39. (New) The system as claimed in claim 36, wherein the component is a semiconductor component.

40. (New) The system as claimed in claim 39, wherein the semiconductor component is a power semiconductor component.

41. (New) The system as claimed in claim 40, wherein the power semiconductor component is a component selected from the group consisting of a diode, a MOSFET, a IGBT, a thyristor and a bipolar transistor.

42. (New) The system as claimed in claim 27, wherein the insulating layer has a plurality of openings arranged in a row or a matrix.

43. (New) The system as claimed in claim 27, wherein the metallization layer is oriented at an angle to the contact surface within a range of from 50° to 70°.

44. (New) The system as claimed in claim 27, wherein the metallization layer has a layer thickness within a range of from 2.0 µm to 20 µm.

45. (New) The system as claimed in claim 27, wherein the insulating layer has a layer thickness within a range of from 50 µm up to and including 200 µm.

46. (New) A method for producing a system comprising:
providing a component with an electrical contact surface;
producing an insulating layer on the component, the insulating layer having an opening to expose and surround a portion of the contact surface of the component so that the contact surface is freely accessible, the insulating layer having a lateral surface that defines the opening; and

locating a metallization layer of a connecting lead on the lateral surface of the insulating layer in such a way that the metallization layer meets the contact surface at an angle less than 90 degrees.

47. (New) The method as claimed in claim 46, wherein the insulating layer is formed by a process comprising:

laminating at least one insulating foil onto the component; and
producing an opening in the insulating foil so that the contact surface of the component is exposed.

48. (New) The method as claimed in claim 47, wherein the insulating foil is laminated under a partial vacuum.

49. (New) The method as claimed in claim 47, wherein the opening in the insulating foil is made by laser ablation.

50. (New) The method as claimed in claim 46, wherein in order to produce the insulating layer on the component, a compressed air process is used wherein a paint is applied to the component.

51. (New) The method as claimed in claim 50, wherein the paint is a photo-sensitive paint.

52. (New) The method as claimed in claim 46, wherein the metallization layer and/or the insulating layer is formed by a vapor deposition method.

53. (New) The method as claimed in claim 46, wherein a section of the connecting lead is formed separately from the metallization layer, the section being produced on the insulating layer to have a thickness which exceeds that of the metallization layer.

54. (New) The method as claimed in claim 53, wherein a metal is electrodeposited to produce the section on the insulating layer.

55. (New) The method as claimed in claim 53, wherein, while the section is being produced, the opening in the insulating layer is closed.